

Features

- Uses CRM(CQ) advanced Trench technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

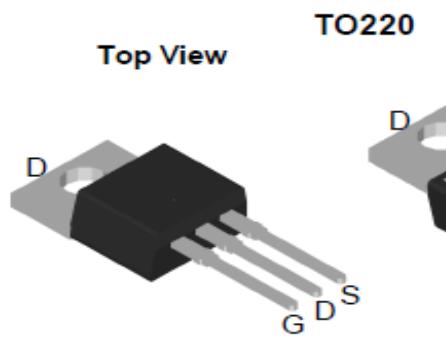
V_{DS}	200V
$R_{DS(on)}$ typ.	30mΩ
I_D	50A

100% DVDS Tested

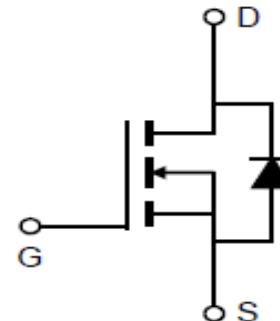
Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

100% Avalanche Tested



Bottom View



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTT360N20N	CRTT360N20N	TO-220	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	50 120 32	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by $T_{j,\max}$)	$I_{D\text{ pulse}}$	200	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	72	mJ
Gate-Source voltage	V_{GS}	± 25	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	236	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	°C

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction - case.	R _{thJC}	0.53	°C/W
Thermal resistance, junction - ambient(min. footprint)	R _{thJA} *	84	

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	200	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2	3	4	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	0.05	1	μA	V _{DS} =200V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	±10	±100	nA	V _{GS} =±25V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	30	36	mΩ	V _{GS} =10V, I _D =30A, T _j =25°C T _j =150°C
Transconductance	g _{fs}	-	74	-	S	V _{DS} =10V, I _D =30A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	2575	-	pF	V _{GS} =0V, V _{DS} =100V, f=1MHz
Output Capacitance	C _{oss}	-	176	-		
Reverse Transfer Capacitance	C _{rss}	-	47	-		
Gate Total Charge	Q _G	-	54	-	nC	V _{GS} =10V, V _{DS} =100V, I _D =30A, f=1MHz
Gate-Source charge	Q _{gs}	-	17	-		
Gate-Drain charge	Q _{gd}	-	18	-		
Turn-on delay time	t _{d(on)}	-	14	-	ns	V _{GS} =10V, V _{DD} =100V, R _{G_ext} =2.7Ω, ID=30A
Rise time	t _r	-	56	-		
Turn-off delay time	t _{d(off)}	-	35	-		
Fall time	t _f	-	51	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz
Gate resistance	R _G	-	1.8	-		

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V _{SD}	-	0.8	1.3	V	V _{GS} =0V, I _{SD} =30A
Body Diode Continuous Forward Current	I _S			50	A	T _c = 25°C
Body Diode Reverse Recovery Time	t _{rr}	-	103	-	ns	I _F =30A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	-	519	-	nC	

*The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.

Typical Performance Characteristics

Fig 1: Output Characteristics

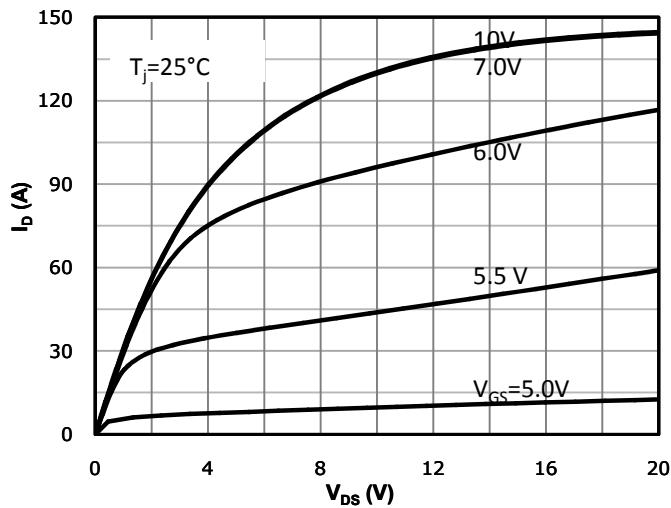


Fig 2: Transfer Characteristics

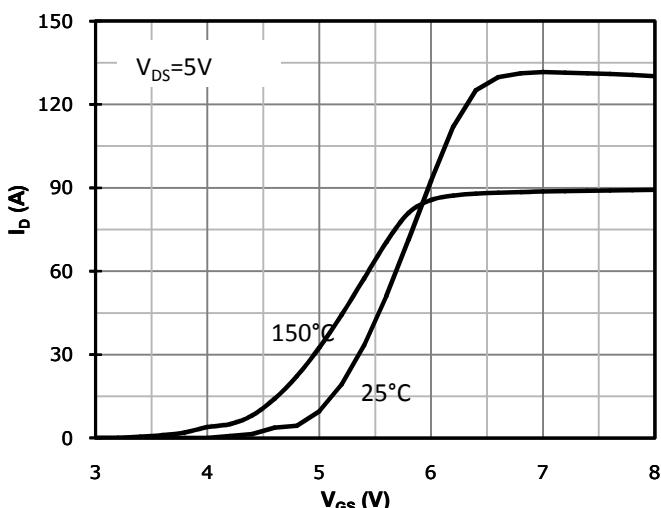
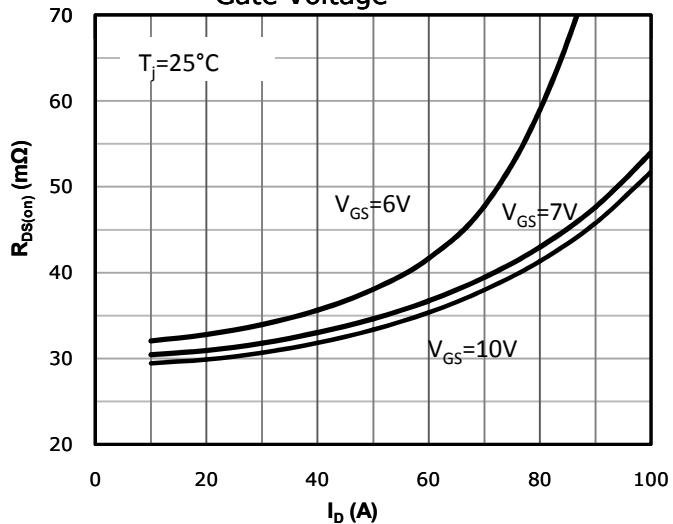
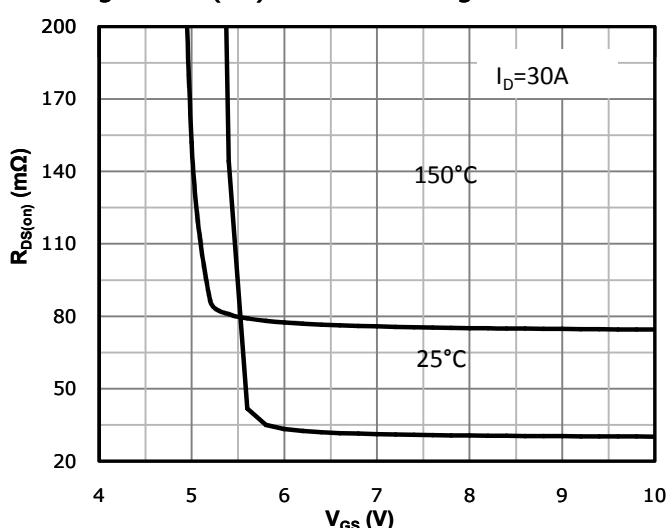
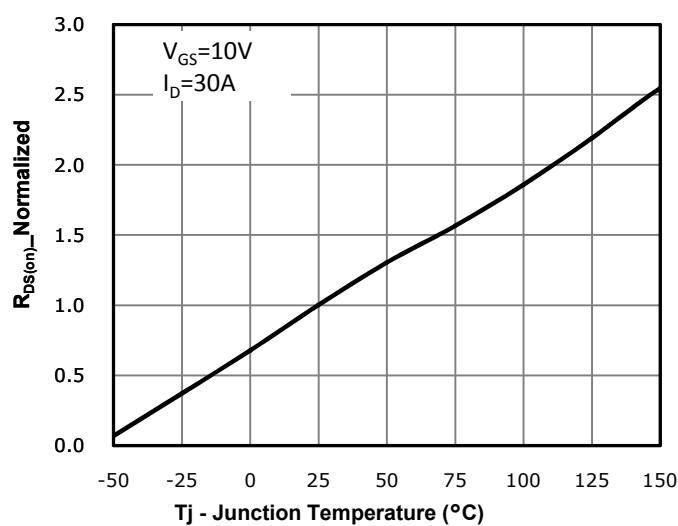

 Fig 3: R_{d(on)} vs Drain Current and Gate Voltage

 Fig 4: R_{d(on)} vs Gate Voltage

 Fig 5: R_{d(on)} vs. Temperature


Fig 6: Capacitance Characteristics

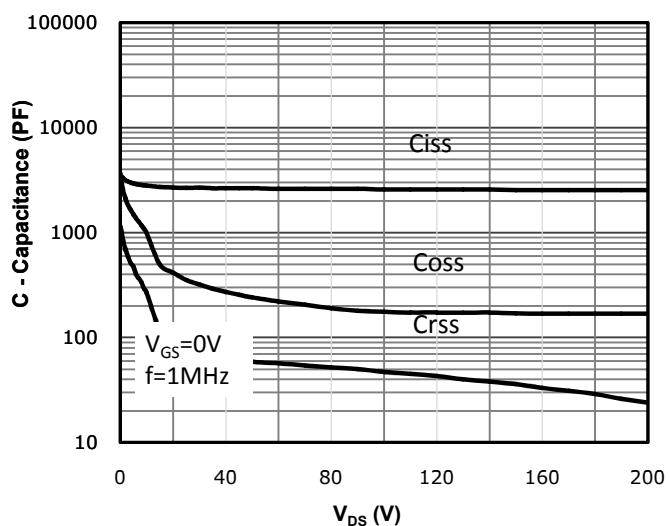


Fig 7: Gate Charge Characteristics

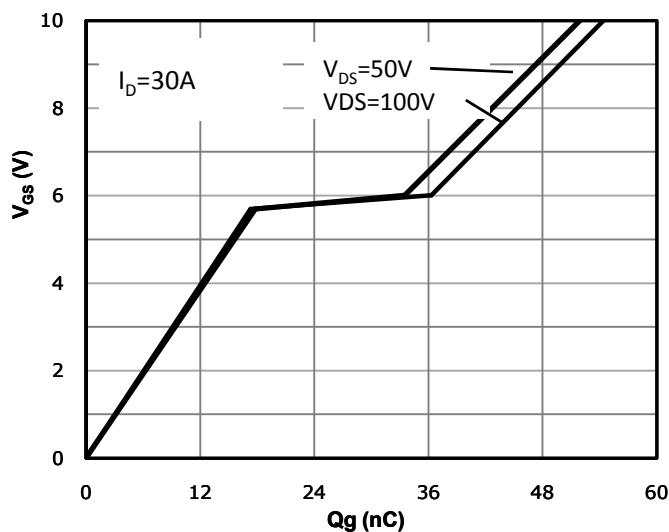


Fig 8: Body-diode Forward Characteristics

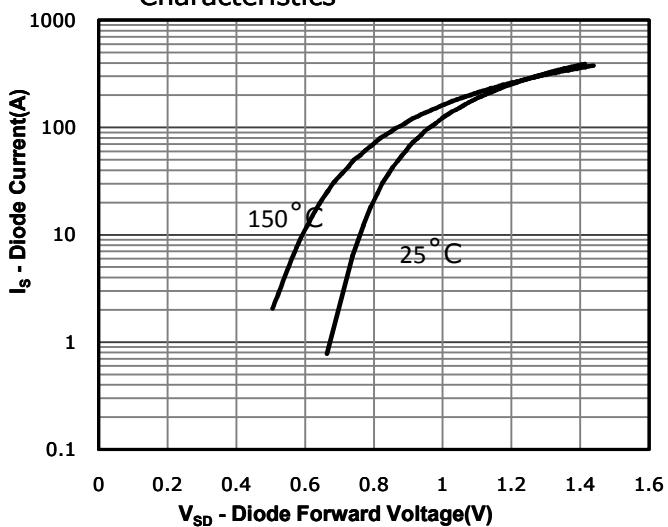


Fig 9: Power Dissipation

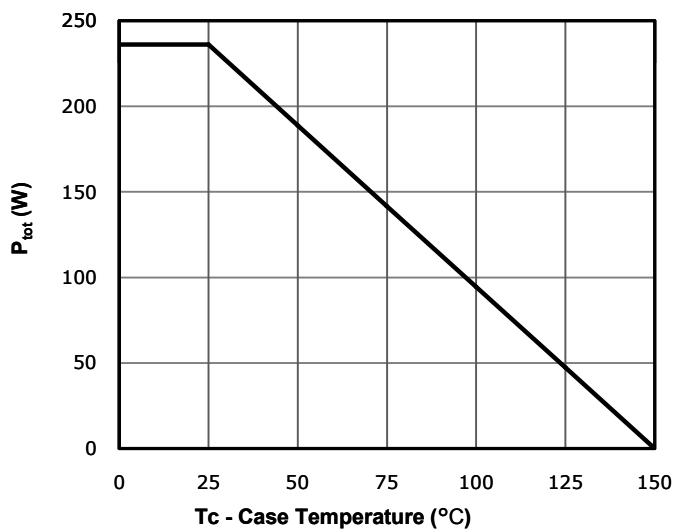


Fig 10: Drain Current Derating

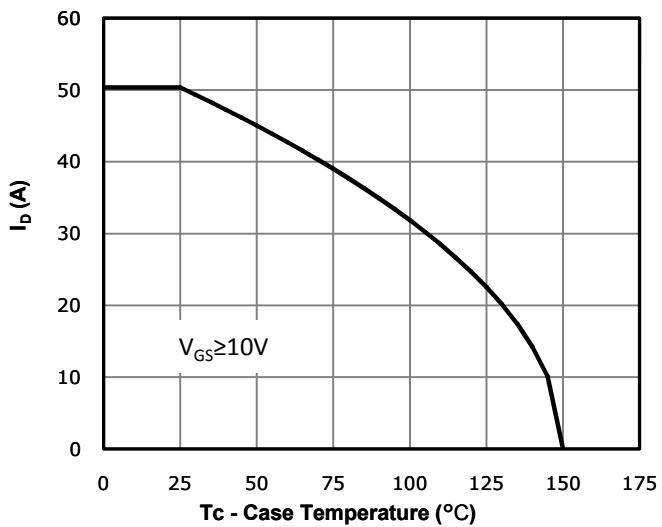


Fig 11: Safe Operating Area

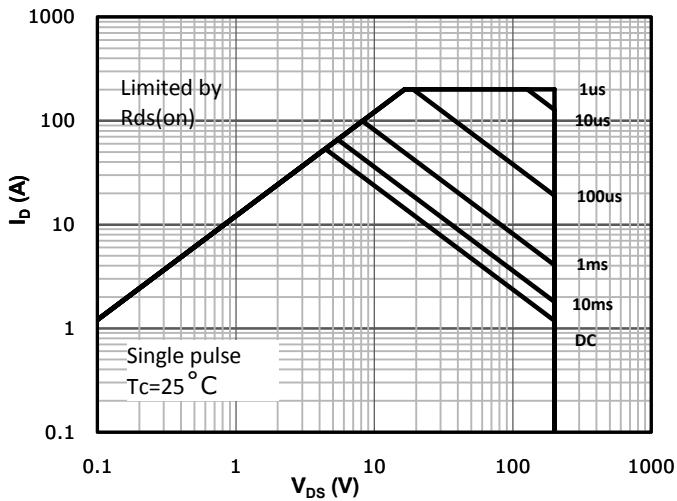
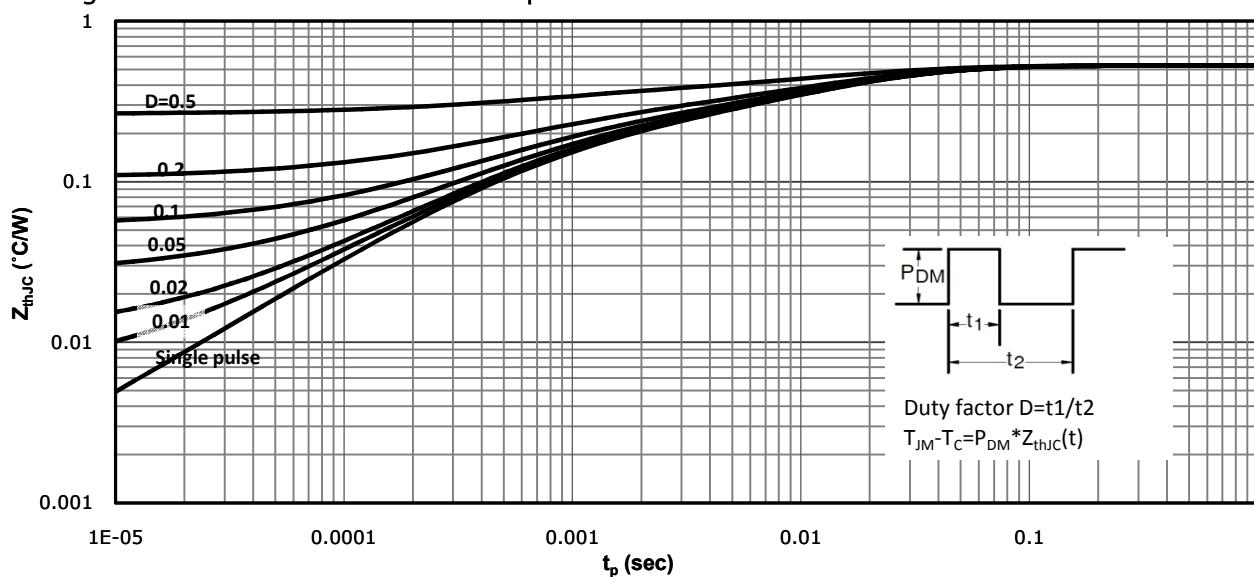
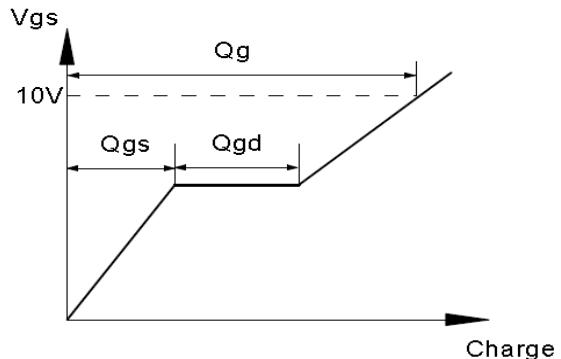
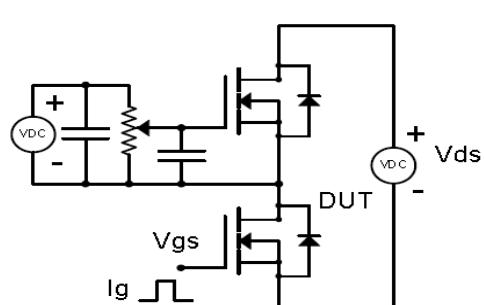


Fig 12: Max. Transient Thermal Impedance

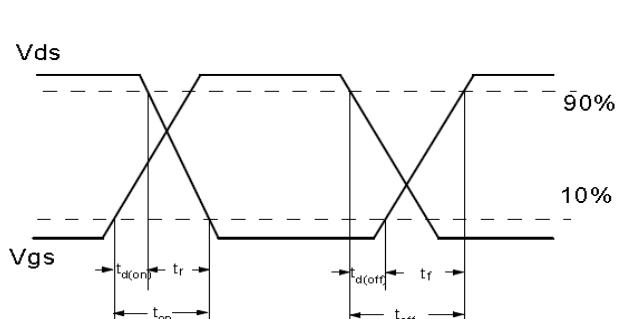
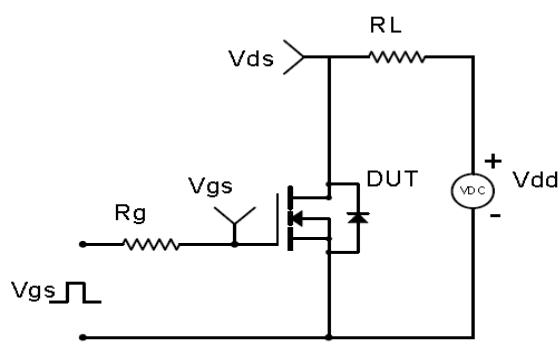


Test Circuit & Waveform

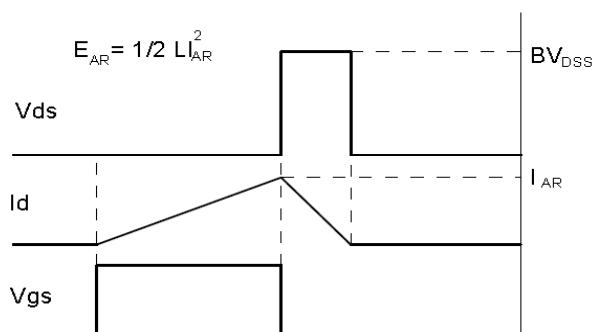
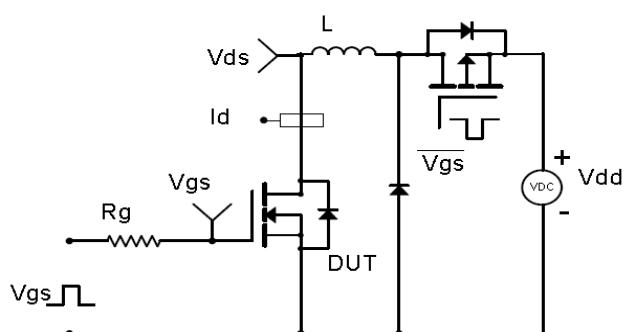
Gate Charge Test Circuit & Waveform



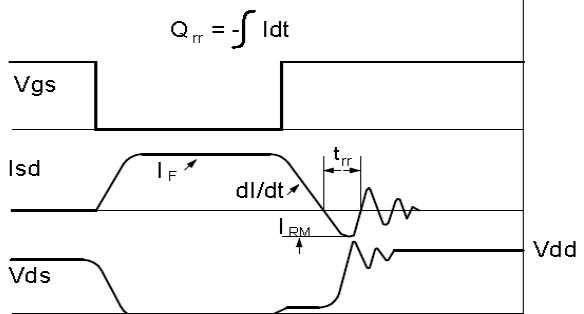
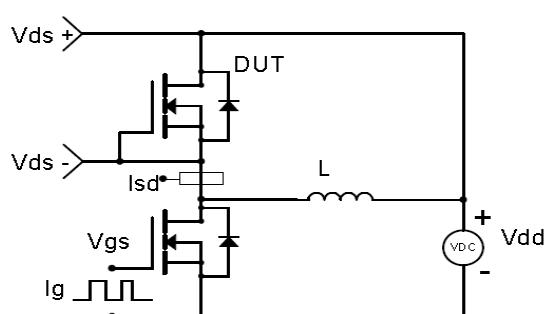
Resistive Switching Test Circuit & Waveforms

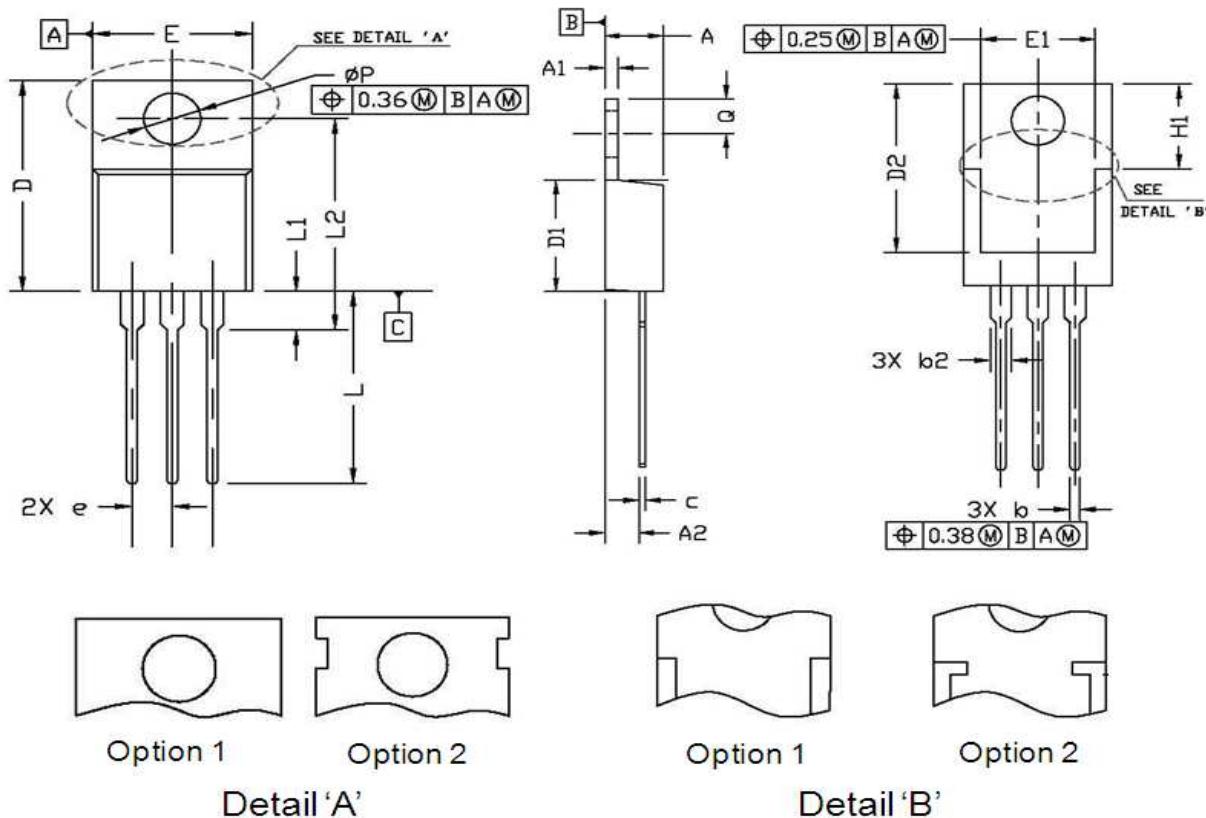


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-220-3L


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.80	0.169	0.189
A1	1.20	1.45	0.047	0.057
A2	2.20	2.90	0.087	0.114
b	0.69	0.95	0.027	0.037
b2	1.00	1.60	0.039	0.063
c	0.33	0.65	0.013	0.026
D	14.70	16.20	0.579	0.638
D1	8.59	9.65	0.338	0.380
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.60	10.60	0.378	0.417
E1	7.00	8.46	0.276	0.333
H1	6.20	7.00	0.244	0.276
L	12.60	14.80	0.496	0.583
L1	2.70	3.80	0.106	0.150
L2	12.13	16.50	0.478	0.650
Q	2.40	3.10	0.094	0.122
P	3.50	3.90	0.138	0.154



华润微电子(重庆)有限公司

CRTT360N20N

Trench N-MOSFET 200V, 30mΩ, 50A

Revision History

Revison	Date	Major changes
1.0	2019/8/23	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.



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